



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



General purpose transistor (dual transistors)

IMX17

●Features

- 1) Two 2SD1484K chips in an SMT package.
- 2) Mounting possible with SMT3 automatic mounting machine.
- 3) Transistor elements are independent, eliminating interference.
- 4) High collector current.
 $I_c = 500\text{mA}$
- 5) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type
NPN silicon transistor

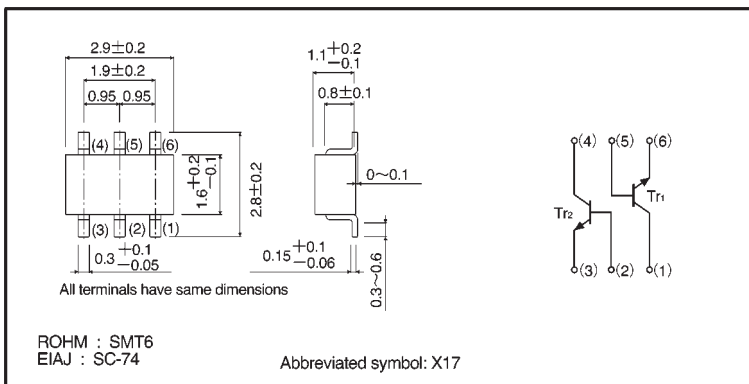
The following characteristics apply to both Tr_1 and Tr_2 .

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_c	500	mA
Power dissipation	P_d	300 (TOTAL)	mW *
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

*200 mW per element must not be exceeded.

●External dimensions (Units: mm)



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	60	—	—	V	$I_C=100\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=100\mu A$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB}=30V$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.6	V	$I_C/I_B=500mA/50mA$
DC current transfer ratio	h_{FE}	120	—	390	—	$V_{CE}=3V, I_C=100mA$ *
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=5V, I_E=-20mA, f=100MHz$
Output capacitance	C_{ob}	—	7	—	pF	$V_{CB}=10V, I_E=0A, f=1MHz$

* Measured using pulse current.

●Packaging specifications

Part No.	Packaging type	Taping
	Code	T110
	Basic ordering unit (pieces)	3000
IMX17		

●Electrical characteristic curves

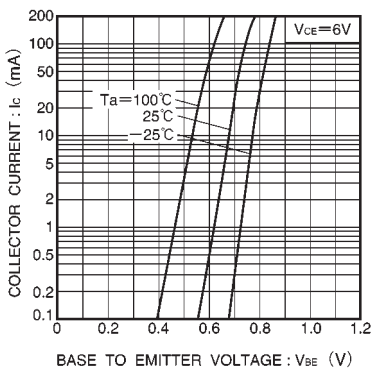


Fig.1 Grounded emitter propagation characteristics

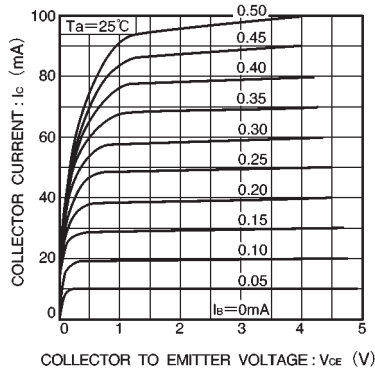


Fig.2 Grounded emitter output characteristics

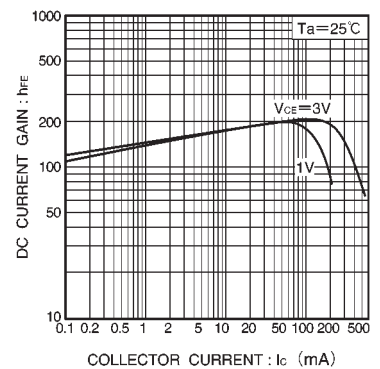


Fig.3 DC current gain vs. collector current (I)

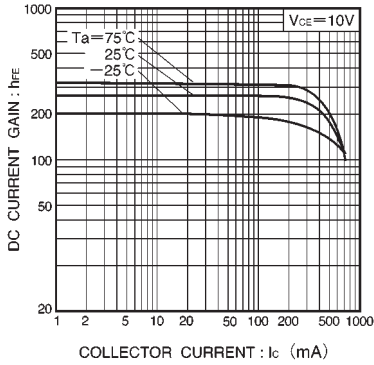


Fig.4 DC current gain vs. collector current (II)

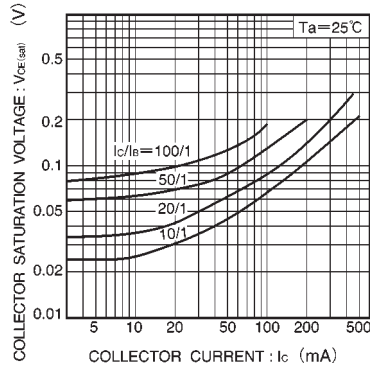


Fig.5 Collector-emitter saturation voltage vs. collector current

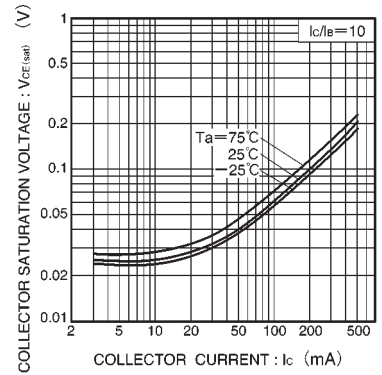


Fig.6 Collector-emitter saturation voltage vs. collector current

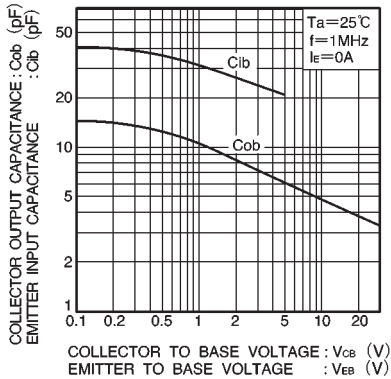


Fig.7 Input/output capacitance vs. voltage

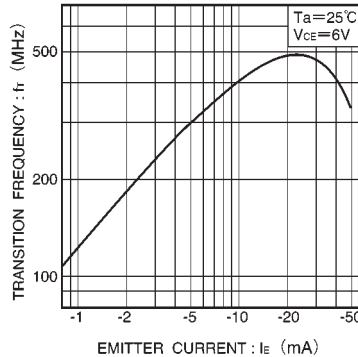


Fig.8 Gain bandwidth product vs. emitter current